



PRELIMINARY AMENDMENT
U.S. Application No. 10/591,987

Attorney Docket No.: Q80398

AMENDMENTS TO THE SPECIFICATION

Please amend the first full paragraph at page 2 with the following amended paragraph:

Conventionally, there is disclosed a technique for forming a light-emitting layer from single $\text{Ga}_Y\text{In}_Z\text{N}$ ($0 \leq Y, Z \leq 1, Y+Z=1$) (see JP-B SHO 55-3834). An example for forming a light-emitting layer from a super lattice structure called quantum well structure is also known (see JP-A 2001-102629). The quantum well structure is a structure in which barrier layers and well layers are alternately stacked periodically (see JP-A 2000-133883). For example, there is disclosed an embodiment in which a $\text{Ga}_{0.7}\text{In}_{0.3}\text{N}$ layer is used as the well layer, and gallium nitride (GaN) is used as the barrier layer, and a light-emitting layer of a multiple quantum well structure is formed (see [embodiment 1] in ~~JP-A 2000-102629~~ JP-A 2001-102629).